

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S6	772	(257/355 or 257/356 or 257/360 or 257/365 or 257/546).ccls. and (ground\$3 with gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/05 08:57
S37	802	(257/355 or 257/356 or 257/360 or 257/365 or 257/546).ccls. and (ground\$4 with gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/05 08:57
S16	261	(semiconductor) and (esd or electro?static) and (ground\$3 with gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET) and ((well or tub or tank) same (ring or isolat\$3)) and (resistor or resistance or resistive) and ((ring or isolat\$3) with (vdd or vss or voltage))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/05 09:00
S38	288	(semiconductor) and (esd or electro?static) and (ground\$3 with gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET) and ((well or tub or tank) same (ring or isolat\$3)) and (resistor or resistance or resistive) and ((ring or isolat\$4) with (vdd or vss or voltage))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/05 09:00
S17	25	(semiconductor) and (esd or electro?static) and (ground\$3 with gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET) and (twin adj wells) and (resistor or resistance or resistive)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/05 09:01
S39	28	(semiconductor) and (esd or electro?static) and (ground\$4 with gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET) and (twin adj wells) and (resistor or resistance or resistive)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/05 09:01
S22	16	(semiconductor) and (esd or electro?static) and (ground\$3 with gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET) and (ring with (PMOSFET or PMOS or PFET or (p near3 (MOS or FET or MOSFET))))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/05 09:02

S40	17	(semiconductor) and (esd or electro?static) and (ground\$4 with gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET) and (ring with (PMOSFET or PMOS or PFET or (p near3 (MOS or FET or MOSFET))))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/05 09:23
S41	127	(semiconductor) and (esd or electro?static) and (ground\$4 with gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET) and (ring with source)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/05 09:25
S42	1126	(semiconductor) and (esd or electro?static) and (ground\$4 with gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET) and (drain with (I/O or pad or input or output))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/05 09:25
S43	3	(semiconductor) and (esd or electro?static) and (ground\$4 with gate or GGMOS or GGMOSFET or GG?FET or GG?MOS or GG?MOSFET) and (gate with vddio)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/05 09:28
S44	1	(semiconductor) and (NMOS with finger) and (gate with vddio) and (PMOSFET or PMOS or P?MOS or P?MOSFET or (p?type near (MOS or MOSFET)))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/05 09:31
S45	11	(semiconductor) and (NMOS) and (gate with vddio) and (PMOSFET or PMOS or P?MOS or P?MOSFET or (p?type near (MOS or MOSFET)))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/05 09:31
S46	11	(semiconductor) and (NMOSFET or NMOS or N?MOS or N?MOSFET or (N?type near (MOS or MOSFET))) and (gate with vddio) and (PMOSFET or PMOS or P?MOS or P?MOSFET or (p?type near (MOS or MOSFET)))	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2005/08/05 09:33